L Number	Hits	Search Text	DB	Time stamp
1	5	current-differenc\$3 NEAR circuit	USPAT;	2003/01/17 18:36
-	- 1		US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
2	7	trans-impedance NEAR stage	USPĀT;	2003/01/17 17:43
-	·		US-PGPUB;	
]			EPO; JPO;	
			IBM TDB	
3	3578	(differential common) NEAR2 feedback	USPAT;	2003/01/17 18:37
3	3376	(differential continon) 1415/1622 recubilent	US-PGPUB;	
			EPO; JPO;	•
			IBM_TDB	
	702	(differential common) NEAR2 (feedback ADJ circuit)	USPAT;	2003/01/17 18:38
4	/02	(differential common) NEAR2 (recadack AD3 circuit)	US-PGPUB;	2005,01,1. 1010
			EPO; JPO;	
			IBM_TDB	
6	0	((differential NEAR2 (feedback ADJ circuit)) WITH (common NEAR2	USPAT;	2003/01/17 18:49
			US-PGPUB;	2003/01/17 10:47
		(feedback ADJ circuit))) and current-steering		
			EPO; JPO;	
		(differential NEAR2 (feedback ADJ circuit)) WITH (common NEAR2	IBM_TDB	2003/01/17 18:42
5	37		USPAT;	2003/01/17 18:42
		(feedback ADJ circuit))	US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	2002/01/17 19:52
7	25	current-steering ADJ circuit	USPAT;	2003/01/17 18:53
			US-PGPUB;	
			EPO; JPO;	
	4		IBM_TDB	
8		(current-steering ADJ circuit) and (reference ADJ circuit)	USPAT;	2003/01/17 18:53
			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
-	1	("4021747").PN.	USPAT;	2003/01/17 12:52
			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
_	17387	circuit same (low NEAR voltage) same (high NEAR voltage)	USPAT;	2003/01/17 12:57
		3 ,	US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
-	252	(circuit same (low NEAR voltage) same (high NEAR voltage)) and (field	USPAT;	2003/01/17 13:01
		NEAR transistor)	US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
_	238	circuit same (low NEAR voltage NEAR (input terminal)) same (high	USPAT;	2003/01/17 14:06
_	236	NEAR voltage NEAR terminal)	US-PGPUB;	
		THE TOTAL COMMING	EPO; JPO;	
			IBM_TDB	
	2	(circuit same (low NEAR voltage NEAR (input terminal)) same (high	USPAT;	2003/01/17 14:23
_	2	NEAR voltage NEAR terminal)) and (field NEAR transistor)	US-PGPUB;	1
1		NEAR VOItage NEAR terminary) and (new NEAR transistor)	EPO; JPO;	
			IBM TDB	
		((-in-wit same (law NEAD walters) same (high NEAD walters)) and (field	USPAT;	2003/01/17 14:03
-	84	((circuit same (low NEAR voltage) same (high NEAR voltage)) and (field NEAR transistor)) and (source NEAR2 drain NEAR2 (gate control))	US-PGPUB;	2005,0171711.05
		NEAR (ransistor)) and (source NEAR2 drain NEAR2 (gate conduit))	EPO; JPO;	
			IBM_TDB	
		(district and (law NEAD valence NEAD (input terminal)) come (high	USPAT;	2003/01/17 14:22
-	21	(circuit same (low NEAR voltage NEAR (input terminal)) same (high	US-PGPUB;	2003/01/17 14.22
		NEAR voltage NEAR terminal)) and (source NEAR2 drain NEAR2	EPO; JPO;	
		(gate control))		
		A STATE OF STREET AND AD	IBM_TDB	2003/01/17 14:09
-	2		USPAT;	2003/01/17 14.09
		voltage NEAR terminal)	US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	

-	0	transistor WITH (low NEAR voltage NEAR input) WITH (high NEAR	USPAT;	2003/01/17 14:10
		voltage NEAR terminal)	US-PGPUB;	
			EPO; JPO;	
			IBM TDB	
-	2	transistor SAME (low NEAR voltage NEAR input) SAME (high NEAR	USPĀT;	2003/01/17 14:14
		voltage NEAR terminal)	US-PGPUB;	
			EPO; JPO;	
			IBM TDB	
-	6	circuit SAME (low NEAR voltage NEAR input) SAME (high NEAR	USPAT;	2003/01/17 14:16
		voltage NEAR terminal)	US-PGPUB;	
		,	EPO; JPO;	
			IBM TDB	
-	2	circuit SAME transistor SAME (low NEAR voltage NEAR input) SAME	USPAT;	2003/01/17 14:19
		(high NEAR voltage NEAR terminal)	US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
-	5905	circuit SAME transistor SAME (low NEAR voltage) SAME (high NEAR	USPAT;	2003/01/17 14:20
		voltage)	US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
-	1564	circuit WITH transistor WITH (low NEAR voltage) WITH (high NEAR	USPAT;	2003/01/17 14:21
		voltage)	US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
-	297	(circuit WITH transistor WITH (low NEAR voltage) WITH (high NEAR	USPAT;	2003/01/17 14:22
		voltage)) and (source NEAR2 drain NEAR2 (gate control))	US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
-	123	((circuit WITH transistor WITH (low NEAR voltage) WITH (high NEAR	USPAT;	2003/01/17 14:23
		voltage)) and (source NEAR2 drain NEAR2 (gate control))) and (field	US-PGPUB;	
		NEAR effect NEAR transistor)	EPO; JPO;	
			IBM_TDB	
-	115	(((circuit WITH transistor WITH (low NEAR voltage) WITH (high	USPAT;	2003/01/17 17:25
		NEAR voltage)) and (source NEAR2 drain NEAR2 (gate control))) and	US-PGPUB;	
		(field NEAR effect NEAR transistor)) and (input terminal)	EPO; JPO;	
			IBM TDB	